Designer's™ Data Sheet

SWITCHMODE™ NPN Silicon Planar Power Transistor

The MJE/MJF18009 has an application specific state—of—the—art die designed for use in 220 V line—operated Switchmode Power supplies and electronic ballast ("light ballast"). These high voltage/high speed transistors exhibit the following main features:

- Improved Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain hff
 - Fast Switching
 - No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Full Characterization at 125°C
- Motorola "6 SIGMA" Philosophy Provides Tight and Reproducible Parametric Distributions
- Specified Dynamic Saturation Data
- Two Package Choices: Standard TO-220 or Isolated TO-220

MAXIMUM RATINGS

Rating	Symbol	MJE18009	MJF18009	Unit
Collector–Emitter Sustaining Voltage	VCEO	450		Vdc
Collector-Emitter Breakdown Voltage	VCES	1000		Vdc
Collector-Base Breakdown Voltage	V _{CBO}	1000		Vdc
Emitter-Base Voltage	V _{EBO}	9		Vdc
Collector Current — Continuous — Peak (1)	I _C	10 20		Adc
Base Current — Continuous — Peak (1)	I _B	4 8		Adc
*Total Device Dissipation @ T _C = 25°C *Derate above 25°C	PD	150 1.2	50 0.4	Watt W/°C
Operating and Storage Temperature	T _J , T _{stg}	-65 to 150		°C
RMS Isolation Voltage (2) Per Figure 22 (1s, 25°C, Humidity \leq 30%) Per Figure 23 TC = 25°C Per Figure 24	VISOL2		4500 3500 1500	V

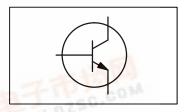
THERMAL CHARACTERISTICS

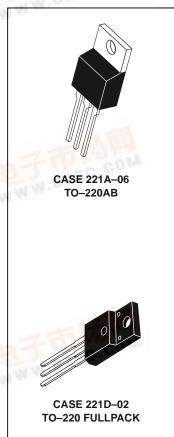
Rating	Symbol	MJE18009	MJF18009	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	R ₀ JC R ₀ JA	0.83 62.5	2.5 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	260		°C

- (1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.
- (2) Proper strike and creepage distance must be provided.

MJE18009 MJF18009

POWER TRANSISTORS 10 AMPERES 1000 VOLTS 50 and 150 WATTS





Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic			Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						•	•	•
Collector–Emitter Sustaining Voltage (I _C = 100 mA, L = 25 mH)				VCEO(sus)	450			Vdc
Collector Cutoff Current (VCE = Rated VCEO, IE				ICEO			100	μAdc
	Collector Cutoff Current (V _{CE} = Rated V _{CES} , V _{EB} = 0) @ T _C = 25°C @ T _C = 125°C (V _{CE} = 800 V, V _{EB} = 0) @ T _C = 125°C @ T _C = 125°C			ICES			100 500 100	μAdc
Emitter–Cutoff Current (VEB = 9 Vdc, I _C = 0)	OL SEE , LB	,		I _{EBO}			100	μAdc
ON CHARACTERISTICS								
Base–Emitter Saturation \ (IC = 3 Adc, IB = 0.3 Ad (IC = 5 Adc, IB = 1 Adc) (IC = 7 Adc, IB = 1.4 Ad	lc)			VBE(sat)		0.8 0.9 0.9	1.1 1.15 1.25	Vdc
Collector–Emitter Saturation Voltage (I _C = 3 Adc, I _B = 0.3 Adc)			@ T _C = 25°C @ T _C = 125°C	VCE(sat)		0.3 0.3	0.6 0.65	Vdc
$(I_C = 5 \text{ Adc}, I_B = 1 \text{ Adc})$			@ T _C = 25°C @ T _C = 125°C			0.3 0.3	0.6 0.65	
$(I_C = 7 \text{ Adc}, I_B = 1.4 \text{ Adc})$			@ T _C = 25°C @ T _C = 125°C			0.35 0.4	0.7 0.9	
DC Current Gain (I _C = 1.5 Adc, V _{CE} = 5 Vdc)			@ T _C = 25°C @ T _C = 125°C	h _{FE}	14	29	34	_
$(I_C = 5 \text{ Adc}, V_{CE} = 1 \text{ Vdc})$			@ T _C = 25°C @ T _C = 125°C		10 8	13 11.5		
$(I_C = 7 \text{ Adc}, V_{CE} = 1 \text{ Vdc})$			@ T _C = 25°C @ T _C = 125°C		7 5	10 7.5		_
$(I_C = 10 \text{ mAdc}, V_{CE} = 5)$	Vdc)		@ T _C = 25°C		10	25		_
DYNAMIC CHARACTERIS	TICS			<u> </u>				•
Current Gain Bandwidth (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1 MHz)			fT		12		MHz	
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1 MHz)			C _{ob}		150	200	pF	
Input Capacitance (VEB = 8 Vdc)				C _{ib}		2750	3500	pF
DYNAMIC SATURATION V	OLTAGE						•	•
Dynamic Saturation Voltage: Determined 1 μs and	I _C = 3 Adc	@ 1 μs	@ T _C = 25°C @ T _C = 125°C	VCE(dsat)		8 13.5		V
		@ 3 μs	@ T _C = 25°C @ T _C = 125°C			4 8		
3 µs respectively after rising I _{B1} reaches 90% of final I _{B1}	I _C = 7 Adc I _{B1} = 1.4 Adc	@ 1 μs	@ T _C = 25°C @ T _C = 125°C			15 21		
20 % or min IR.I	V _{CC} = 300 V	@ 3 μs	@ T _C = 25°C @ T _C = 125°C			2 2.7		

0 H. I.D. I.D. T. I. D. I.D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

	Characteristic	Symbol	Min	Тур	Max	Unit	
WITCHING CHARAC	TERISTICS: Resistive Load (D.C.	≤ 10%, Pulse Width	= 20 μs)				
Turn-on Time	I _C = 3 Adc, I _{B1} = 0.3 Adc	@ T _C = 25°C @ T _C = 125°C	t _{on}		220 220	300	ns
Turn-off Time	I _{B2} = 1.5 Adc V _{CC} = 300 Vdc	@ T _C = 25°C @ T _C = 125°C	^t off		1.28 1.6	2.5	μs
Turn-on Time	I _C = 5 Adc, I _{B1} = 1 Adc	@ T _C = 25°C @ T _C = 125°C	ton		120 350	250	ns
Turn-off Time	I _{B2} = 2.5 Adc V _{CC} = 300 Vdc	@ T _C = 25°C @ T _C = 125°C	t _{off}		2.2 2.6	2.5	μs
Turn-on Time	I _C = 7 Adc, I _{B1} = 1.4 Adc	@ T _C = 25°C @ T _C = 125°C	t _{on}		175 500	300	ns
Turn-off Time	I _{B2} = 3.5 Adc V _{CC} = 300 Vdc	@ T _C = 25°C @ T _C = 125°C	^t off		1.75 2.1	2.5	μs
WITCHING CHARAC	TERISTICS: Inductive Load (V _{clai}	mp = 300 V, V _{CC} =	15 V, L = 200 μ	.H)	•	•	
Fall Time		@ T _C = 25°C @ T _C = 125°C	t _f		110 125	200	ns
Storage Time	I _C = 3 Adc I _{B1} = 0.3 Adc I _{B2} = 1.5 Adc	@ T _C = 25°C @ T _C = 125°C	t _S		2 2.6	2.75	μs
Crossover Time	.62	@ T _C = 25°C @ T _C = 125°C	t _C		250 300	350	ns
Fall Time		@ T _C = 25°C @ T _C = 125°C	t _f		110 135	200	ns
Storage Time	I _C = 5 Adc I _{B1} = 1 Adc I _{B2} = 2.5 Adc	@ T _C = 25°C @ T _C = 125°C	t _S		2.4 3.1	3.5	μs
Crossover Time	- IB2 = 2.0 / NO	@ T _C = 25°C @ T _C = 125°C	t _C		260 300	350	ns
Fall Time		@ T _C = 25°C @ T _C = 125°C	tf		105 150	200	ns
Storage Time	I _C = 7 Adc I _{B1} = 1.4 Adc I _{B2} = 3.5 Adc	@ T _C = 25°C @ T _C = 125°C	t _S		1.75 2.25	2.75	μs
Crossover Time	- IBZ = 0.0 / 100	@ T _C = 25°C @ T _C = 125°C	t _C		225 300	350	ns

TYPICAL STATIC CHARACTERISTICS

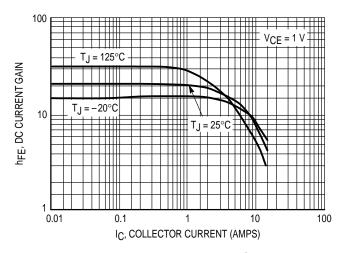


Figure 1. DC Current Gain @ 1 Volt

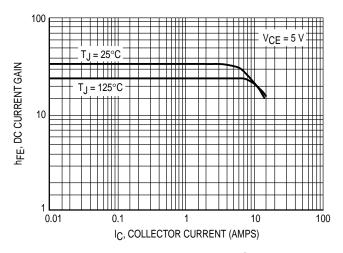


Figure 2. DC Current Gain @ 5 Volt

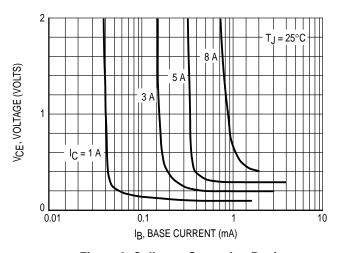


Figure 3. Collector Saturation Region

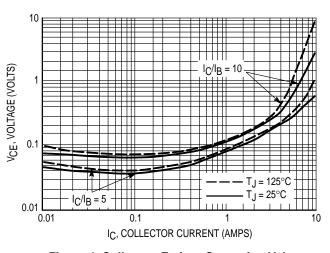


Figure 4. Collector-Emitter Saturation Voltage

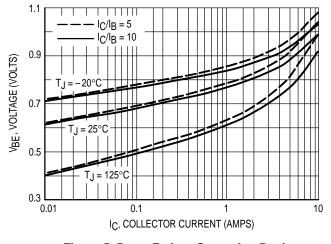


Figure 5. Base-Emitter Saturation Region

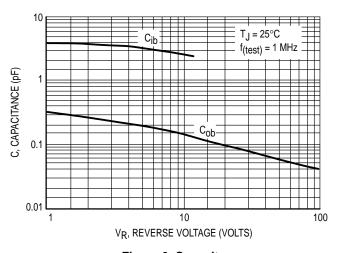


Figure 6. Capacitance

TYPICAL SWITCHING CHARACTERISTICS

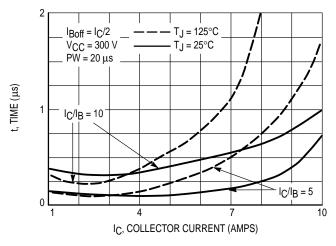


Figure 7. Resistive Switching, ton

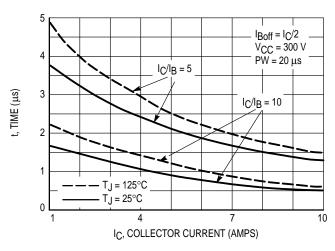


Figure 8. Resistive Switching, toff

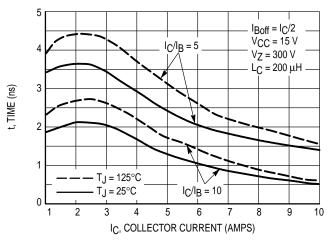


Figure 9. Inductive Storage Time, tsi

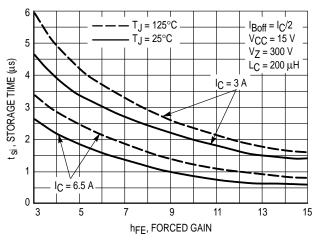


Figure 10. Inductive Storage Time

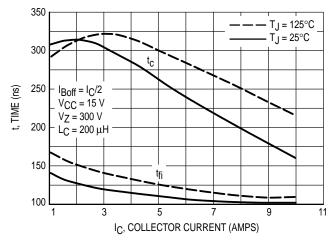


Figure 11. Inductive Switching, $t_C \& t_{fi} @ I_C/I_B = 5$

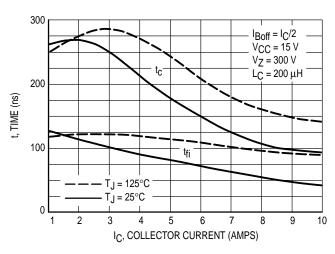
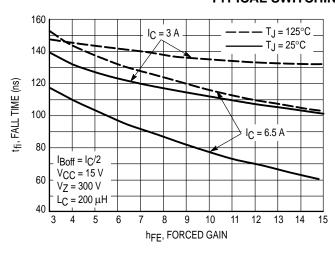


Figure 12. Inductive Switching, $t_C \& t_{fi} @ I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS



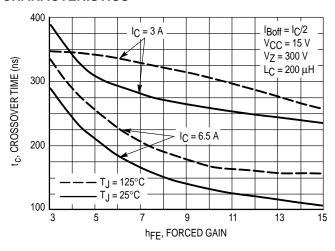


Figure 13. Inductive Fall Time

Figure 14. Inductive Crossover Time

TYPICAL CHARACTERISTICS

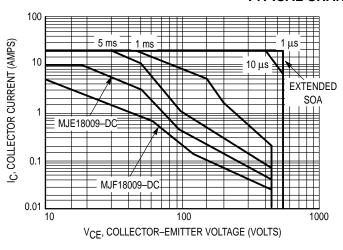


Figure 15. Forward Bias Safe Operating Area

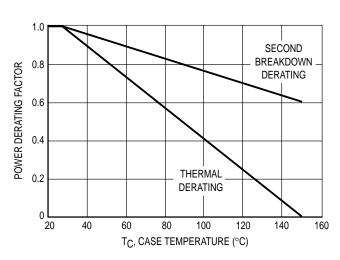


Figure 17. Forward Bias Power Derating

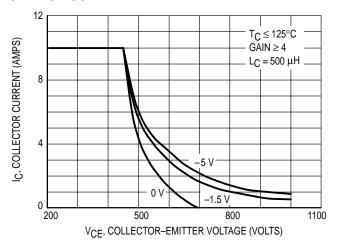
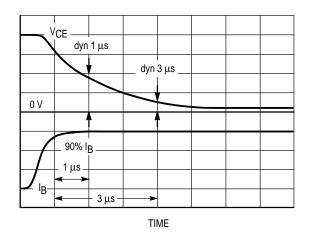


Figure 16. Reverse Bias Switching Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_{C} – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on $T_{C} = 25^{\circ}C$; $T_{J}(pk)$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_{C} > 25^{\circ}C$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17.

TJ(pk) may be calculated from the data in Figures 20 and 21. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn–off with the base–to–emitter junction reverse biased. The safe level is specified as a reverse–biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

TYPICAL SWITCHING CHARACTERISTICS (IB = IC/2 FOR ALL CURVES)



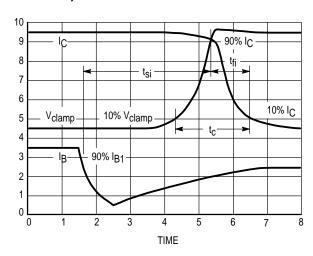
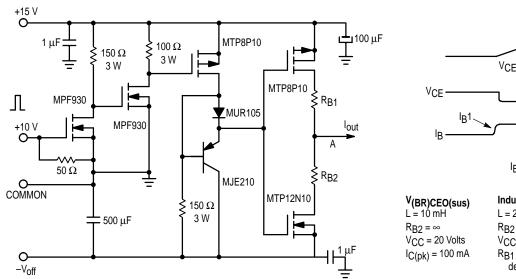
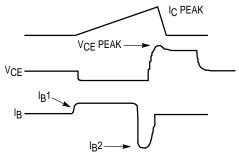


Figure 18. Dynamic Saturation Voltage Measurements

Figure 19. Inductive Switching Measurements

Table 1. Inductive Load Switching Drive Circuit





TYPICAL THERMAL RESPONSE (IB = IC/2 FOR ALL CURVES)

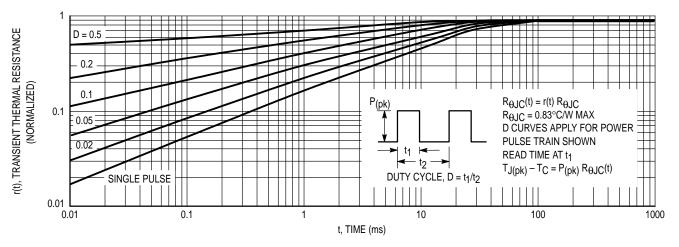


Figure 20. Typical Thermal Response (Z_θJC(t)) for MJE18009

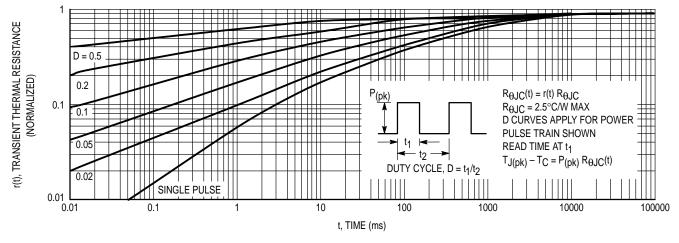
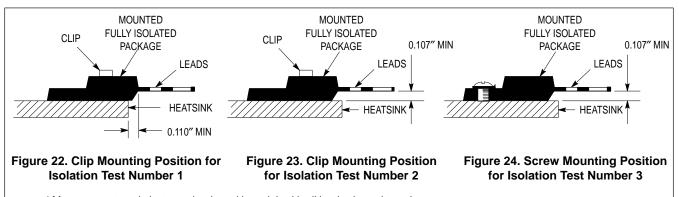


Figure 21. Typical Thermal Response (Z_θJC(t)) for MJF18009

TEST CONDITIONS FOR ISOLATION TESTS*



^{*} Measurement made between leads and heatsink with all leads shorted together

MOUNTING INFORMATION**

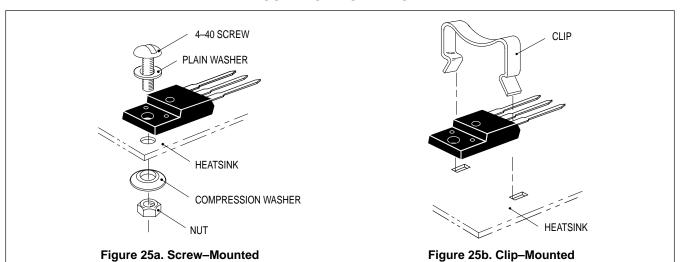


Figure 25. Typical Mounting Techniques for Isolated Package

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in - lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

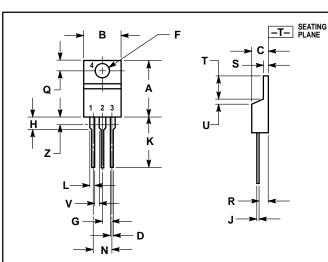
Destructive laboratory tests show that using a hex head 4–40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4–40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, Motorola does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

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^{**} For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS



NOTES:

- NOTES.

 1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2 CONTROLLING DIMENSION: INCH.

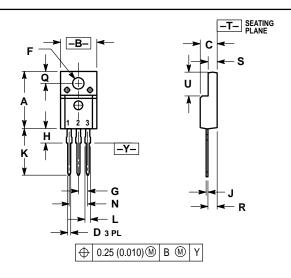
 3 DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. BASE

- COLLECTOR
- 3. EMITTER 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.621	0.629	15.78	15.97	
В	0.394	0.402	10.01	10.21	
С	0.181	0.189	4.60	4.80	
D	0.026	0.034	0.67	0.86	
F	0.121	0.129	3.08	3.27	
G	0.100	BSC	2.54 BSC		
Н	0.123	0.129	3.13	3.27	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.14	1.52	
N	0.200	BSC	5.08	BSC	
Q	0.126	0.134	3.21	3.40	
R	0.107	0.111	2.72	2.81	
S	0.096	0.104	2.44	2.64	
U	0.259	0.267	6.58	6.78	

STYLE 1: PIN 1. GATE

2. DRAIN 3. SOURCE

CASE 221D-02 (ISOLATED TO-220 TYPE) **UL RECOGNIZED: FILE #E69369 ISSUE D**

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